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Substitute for form 1449A/B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	09/940,792-Conf.#5268
		Filing Date	August 29, 2001
		First Named Inventor	Paul A. Farrar et al.
		Art Unit	2815
		Examiner Name	E.C.H. Lee
		Attorney Docket Number	M4065.0382/P382-A
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Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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**INFORMATION DISCLOSURE
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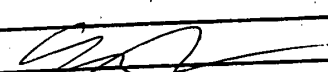
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)					
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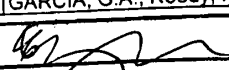
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language translation is attached.

Examiner Signature		Date Considered	8/13/06
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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	Application Number	09/940,792-Conf.#5268		
	Filing Date	August 29, 2001		
	First Named Inventor	Paul A. Farrar et al.		
	Art Unit	2815		
	Examiner Name	E.C.H. Lee		
	Attorney Docket Number	M4065.0382/P382-A		
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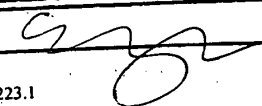
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		First Named Inventor	Paul A. Farrar et al.		
		Art Unit	2815		
		Examiner Name	E.C.H. Lee		
Sheet	9	of	11	Attorney Docket Number	M4065.0382/P382-A


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Art Unit	2815				
Examiner Name	E.C.H. Lee				
Attorney Docket Number	M4065.0382/P382-A				
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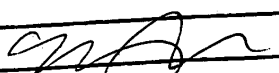
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		Filing Date	August 29, 2001
		First Named Inventor	Paul A. Farrar
		Group Art Unit	<i>2812-2815</i>
		Examiner Name	<i>D. Zarnke Lee</i>
Sheet	1	of	1
		Attorney Docket Number	M4065.0382/P382-A

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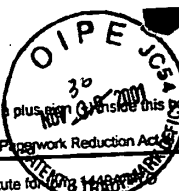
U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
<i>W</i>	A	5,920,121		Forbes, et al.*	07/06/1999
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		Examiner Name	B. Zameke Lee
Attorney Docket Number	M4065.0382/P382-A		
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U.S. PATENT DOCUMENTS						
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		Number	Kind Code ² (if known)			
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/940,792
		Filing Date	August 29, 2001
		First Named Inventor	Paul A. Farrar
		Group Art Unit	2012 2815
		Examiner Name	D. Zameke Lee
Sheet 2 of 2	Attorney Docket Number	M4065.0382/P382-A	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	²
CL	B	F.A. Nichols, et al. - "Surface- (Interface-) and Volume-Diffusion Contributions to Morphological Changes Driven by Capillarity," Transactions of the Metallurgical Society of AIME, Volume 233, October 1965, pgs. 1840-1848*	
CL	C	Tsutomu Sato, et al. - "A New Substrate Engineering for the Formation of Empty Space in Silicon (ESS) Induced by Silicon Surface Migration," 1999 IEEE, pgs. 517-520*	
CL	D	U.S. Application, Serial No. 09/069,346 filed April 29, 1998, Attorney docket #303.367US1, pgs. 1-22 w/6 shts. drwgs.*	

Examiner Signature		Date Considered	9/16/02
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